# NPN power transistor Rev. 02 — 29 July 2010

**Product data sheet** 

#### **Product profile** 1.

## 1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) 3 leads plastic package.

### 1.2 Features and benefits

Fast switching

■ High voltage capability of 700 V

#### 1.3 **Applications**

- Compact fluorescent lamps (CFL)
- Electronic lighting ballasts
- Inverters
- Off-line self-oscillating power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Ic	collector current	DC; see Figure 2	-	-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; see <u>Figure 1</u>	-	-	2.1	W
V <sub>CESM</sub>	collector-emitter peak voltage	$V_{BE} = 0 V$		-11	700	٧
Static chara	acteristics					
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 0.8 A; $T_{lead}$ = 25 °C; see <u>Figure 8</u> ; see <u>Figure 9</u>	5	7.5	20	





# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector		C I
3	E	emitter		BE sym123
			SOT54 (TO-92)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUJ100LR	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	700	V
V <sub>CBO</sub>	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
V <sub>CEO</sub>	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
I <sub>C</sub>	collector current	DC; see Figure 2	-	1	Α
I <sub>CM</sub>	peak collector current		-	2	Α
I <sub>B</sub>	base current	DC	-	0.5	Α
I <sub>BM</sub>	peak base current		-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; see <u>Figure 1</u>	-	2.1	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
V <sub>EBO</sub>	emitter-base voltage	I <sub>C</sub> = 0 A; I(Emitter) = 10 mA	-	9	V

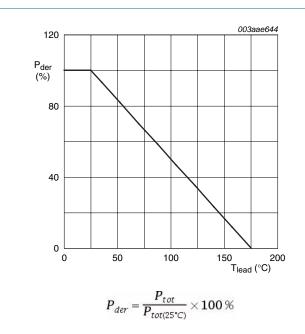
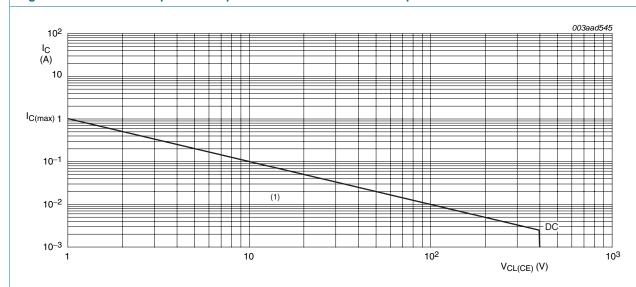


Fig 1. Normalized total power dissipation as a function of lead temperature



 $T_{lead} \le 25$  °C(1) Region of permissible DC operation

Fig 2. Forward bias safe operating area

# 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	see Figure 3	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed-circuit board mounted; lead length 4 mm	-	150	-	K/W

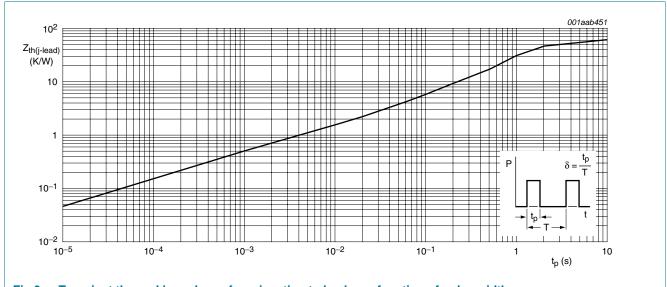
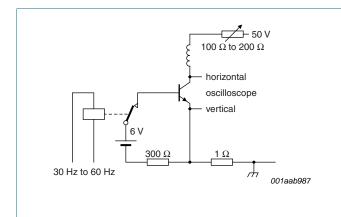


Fig 3. Transient thermal impedance from junction to lead as a function of pulse width

# 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
I <sub>CES</sub>	collector-emitter cut-off current	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 125 \text{ °C}$	-	-	5	mA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 \text{ °C}$	-	-	1	mA
V <sub>CEOsus</sub>	collector-emitter sustaining voltage	$I_B = 0 \text{ A}$ ; $I_C = 1 \text{ mA}$ ; $L_C = 25 \text{ mH}$ ; $T_{lead} = 25 \text{ °C}$ ; see <u>Figure 4</u> ; see <u>Figure 5</u>	400	-	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 0.25 A; $I_B$ = 50 mA; $T_{lead}$ = 25 °C; see Figure 6	-	0.2	0.5	V
		$I_C$ = 0.5 A; $I_B$ = 125 mA; $T_{lead}$ = 25 °C; see Figure 6	-	0.3	1	V
		$I_C$ = 0.75 A; $I_B$ = 250 mA; $T_{lead}$ = 25 °C; see Figure 6	-	0.4	1.5	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 0.25 A; $I_B$ = 50 mA; $T_{lead}$ = 25 °C; see Figure 7	-	-	1	V
		$I_C$ = 0.5 A; $I_B$ = 125 mA; $T_{lead}$ = 25 °C; see Figure 7	-	-	1.2	V
h <sub>FE</sub>	DC current gain	$I_C = 0.5 \text{ mA}$ ; $V_{CE} = 2 \text{ V}$ ; $T_{lead} = 25 \text{ °C}$	12	-	-	
		$I_C = 0.4 \text{ A}$ ; $V_{CE} = 5 \text{ V}$ ; $T_{lead} = 25 \text{ °C}$ ; 10 - see Figure 8; see Figure 9	-	30		
		$I_C = 0.8 \text{ A}$ ; $V_{CE} = 5 \text{ V}$ ; $T_{lead} = 25 \text{ °C}$ ; see <u>Figure 8</u> ; see <u>Figure 9</u>	5	7.5	20	
Dynamic cha	racteristics					
t <sub>f</sub>	fall time	$I_C$ = 1 A; $I_{Bon}$ = 200 mA; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{lead}$ = 25 °C; inductive load; see Figure 10; see Figure 11	-	80	-	ns



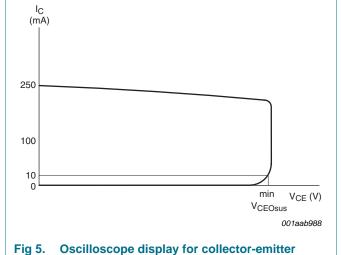


Fig 4. Test circuit for collector-emitter sustaining voltage

Oscilloscope display for collector-emitter sustaining voltage test waveform

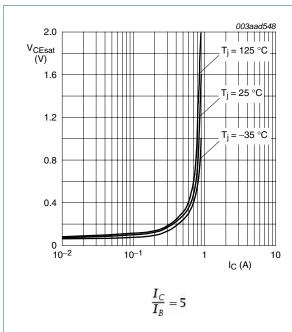


Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values

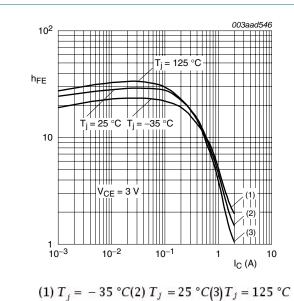


Fig 8. DC current gain as a function of collector current; typical values

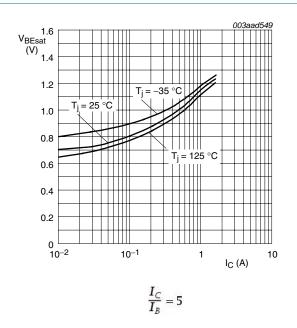
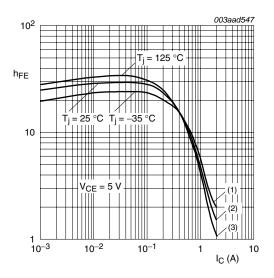
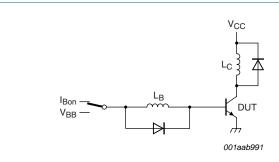


Fig 7. Base-emitter saturation voltage as a function of collector current; typical values



(1)  $T_j = -35 \,^{\circ}C(2) \, T_j = 25 \,^{\circ}C(3) \, T_j = 125 \,^{\circ}C$ 

Fig 9. DC current gain as a function of collector current; typical values



$$V_{CC}=300~V;\,V_{BB}=\,-\,5~V;L_C=200~\mu H;L_B=1\,\mu H$$

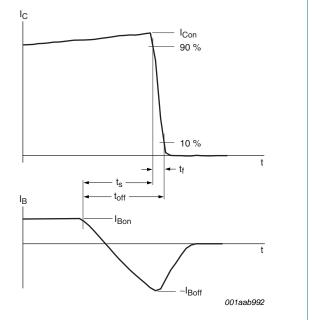


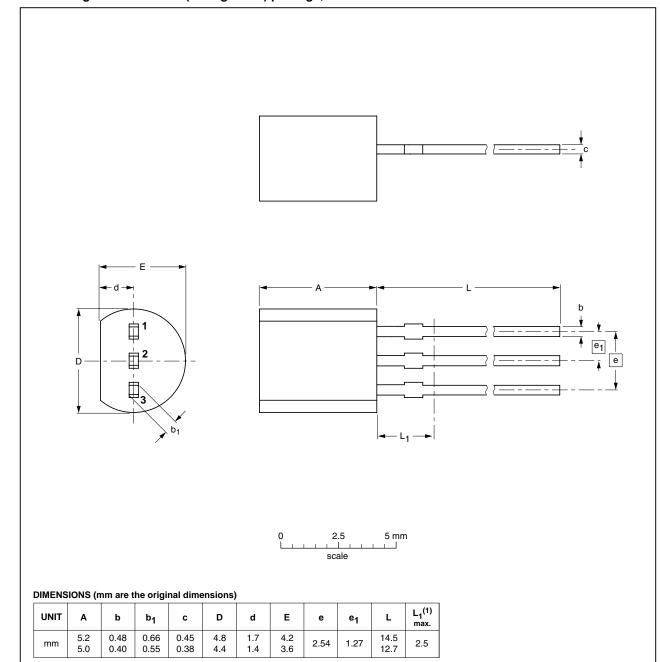
Fig 10. Test circuit for inductive load switching

Fig 11. Switching times waveforms for inductive load

# 7. Package outline

### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A		<del>-04-06-28</del> -04-11-16

Fig 12. Package outline SOT54 (TO-92)

BUJ100LR



# 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ100LR v.2	20100729	Product data sheet	-	BUJ100LR v.1
Modifications:	<ul> <li>Various changes to</li> </ul>	content.		
BUJ100LR v.1	20090812	Product data sheet	-	-

# 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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# **BUJ100LR**

### **NPN** power transistor

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